

HiPerFRED

 V_{RRM} 1200 V

30 A I_{FAV}

35 ns

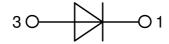
High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

DSEP29-12B



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

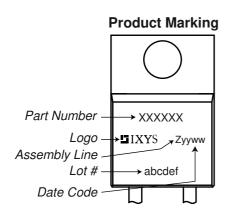
20170803b



Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V _{RRM}	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			1200	V
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			100	μΑ
		$V_{R} = 1200 \text{ V}$	$T_{VJ} = 150$ °C			0.5	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			3.76	V
		$I_F = 60 \text{ A}$				4.66	٧
		I _F = 30 A	T _{vJ} = 150°C			2.31	V
		$I_F = 60 \text{ A}$				3.11	٧
I _{FAV}	average forward current	T _C = 100°C	T _{vJ} = 175°C			30	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage	an advidation and	$T_{VJ} = 175$ °C			1.26	V
\mathbf{r}_{F}	slope resistance	ss calculation only				25.4	mΩ
R _{thJC}	thermal resistance junction to case	9				0.9	K/W
R _{thCH}	thermal resistance case to heatsin	ık			0.50		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			165	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α
CJ	junction capacitance	$V_R = 600 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		12		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		12.5		Α
		$I_F = 30 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 125^{\circ}C$		18		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 30 \text{ A; } V_R = 600 \text{ V} \\ -di_F /dt = 400 \text{ A/} \mu\text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		140		ns
	,	1	$T_{VJ} = 125^{\circ}C$		480		ns



Package TO-220				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal			35	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				2		g	
M _D	mounting torque		0.4		0.6	Nm	
F _c	mounting force with clip		20		60	N	



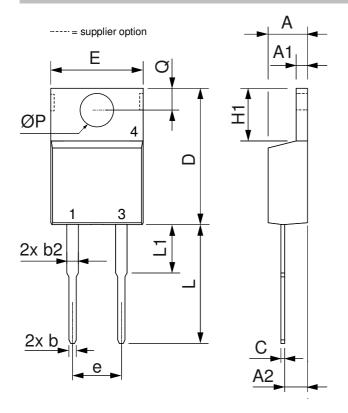
Or	dering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Sta	andard	DSEP29-12B	DSEP29-12B	Tube	50	501196

Similar Part	Package	Voltage class
DSEP29-12A	TO-220AC (2)	1200

Equiva	alent Circuits for	Simulation	* on die level	T _{vJ} = 175 °C
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	1.26		V
$R_{0 \text{ max}}$	slope resistance *	22.6		$m\Omega$



Outlines TO-220



Dim.	Millimeter		Inches		
	Min.	Max.	Min.	Max.	
Α	4.32	4.82	0.170	0.190	
A1	1.14	1.39	0.045	0.055	
A2	2.29	2.79	0.090	0.110	
b	0.64	1.01	0.025	0.040	
b2	1.15	1.65	0.045	0.065	
С	0.35	0.56	0.014	0.022	
D	14.73	16.00	0.580	0.630	
E	9.91	10.66	0.390	0.420	
е	5.08	BSC	0.200	BSC	
H1	5.85	6.85	0.230	0.270	
L	12.70	13.97	0.500	0.550	
L1	2.79	5.84	0.110	0.230	
ØP	3.54	4.08	0.139	0.161	
Q	2.54	3.18	0.100	0.125	





Fast Diode

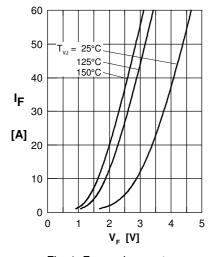


Fig. 1 Forward current I_F versus V_F

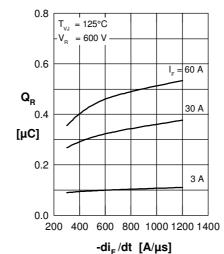
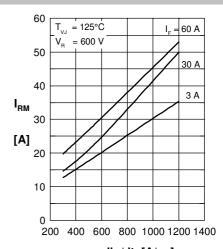


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$



-di_F/dt [A/μs] Fig. 3 Typ. peak reverse current I_{RM} versus -di_F/dt

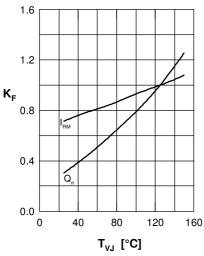


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

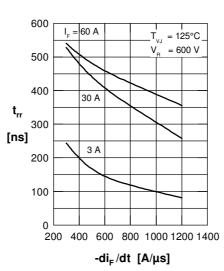


Fig. 5 Typ. recovery time t_{rr} versus $-di_{F}/dt$

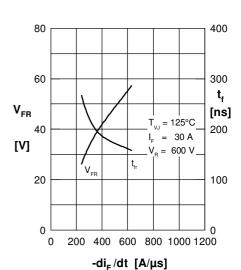


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

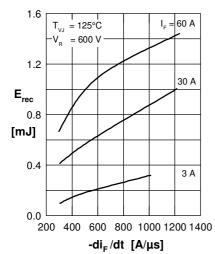


Fig. 7 Typ. recovery energy $E_{\rm rec}$ versus $-di_{\rm F}/dt$

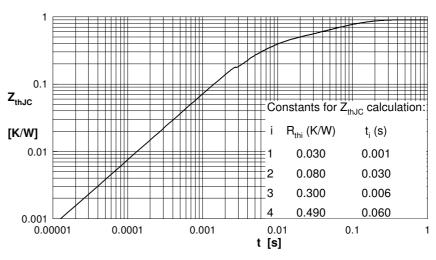


Fig. 8 Transient thermal resistance junction to case

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Discrete Semiconductor Modules category:

Click to view products by IXYS manufacturer:

Other Similar products are found below:

M252511FV DD260N12K-A DD380N16A DD89N1600K-A APT2X21DC60J APT58M80J B522F-2-YEC MSTC90-16 ND104N16K 25.163.0653.1 25.163.2453.0 25.163.4253.0 25.190.2053.0 25.194.3453.0 25.320.4853.1 25.320.5253.1 25.326.3253.1 25.326.3553.1 25.330.1653.1 25.330.4753.1 25.330.5253.1 25.334.3253.1 25.334.3353.1 25.350.2053.0 25.352.4753.1 25.522.3253.0 T483C T484C T485F T485H T512F-YEB T513F T514F T554 T612FSE 25.161.3453.0 25.179.2253.0 25.194.3253.0 25.352.1253.1 25.326.4253.1 25.330.0953.1 25.332.4353.1 25.350.1653.0 25.350.2453.0 25.352.1453.0 25.352.1453.0 25.352.2453.0 25.352.5453.1 25.522.3353.0 25.602.4053.0